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[MITB10WB1200TMH](#)

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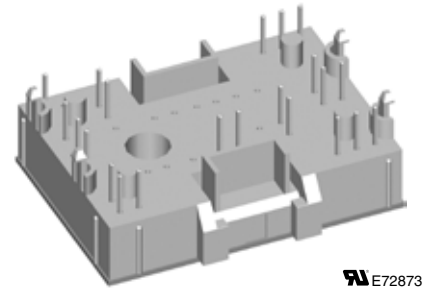
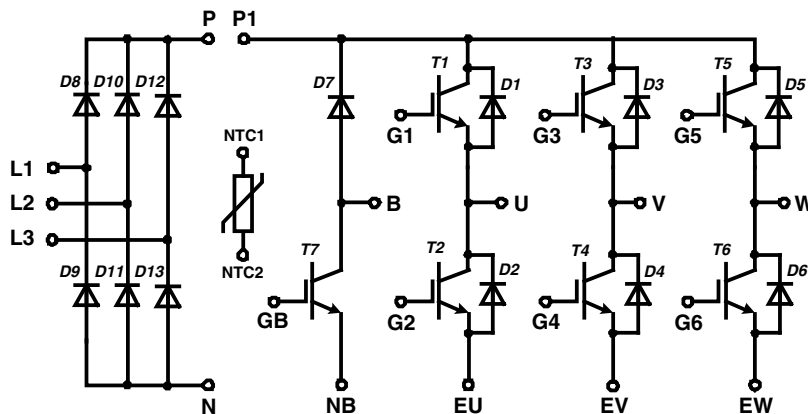
Converter - Brake - Inverter Module

Low Loss Trench IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600\text{ V}$	$V_{CES} = 1200\text{ V}$	$V_{CES} = 1200\text{ V}$
$I_{DAVM25} = 90\text{ A}$	$I_{C25} = 17\text{ A}$	$I_{C25} = 17\text{ A}$
$I_{FSM} = 300\text{ A}$	$V_{CE(sat)} = 1.9\text{ V}$	$V_{CE(sat)} = 1.9\text{ V}$

Part name (Marking on product)

MITB10WB1200TMH



Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with low loss Trench IGBTs
 - very low saturation voltage
 - positive temperature coefficient
 - short tail current
- Epitaxial free wheeling diodes with hiperfast soft reverse recovery
- Temperature sense included

Application:

- AC motor drives
- Pumps, Fans
- Washing machines
- Air-conditioning system
- Inverter and power supplies

Package:

- "Mini" package
- Assembly height is 17 mm
- Insulated base plate
- Pins suitable for wave soldering and PCB mounting
- Assembly clips available
 - IXKU 5-505 screw clamp
 - IXRB 5-506 click clamp
- UL registered E72873

Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage		$T_{VJ} = 150^{\circ}\text{C}$		1200	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$		17	A	
I_{C80}			$T_C = 80^{\circ}\text{C}$		12	A	
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		70	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.9 2.3	2.2	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.3\text{ A}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	5	5.5	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		0.8	0.6	mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			150	nA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$			600	pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$			54	nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 25^{\circ}\text{C}$		55	ns	
t_r	current rise time				30	ns	
$t_{d(off)}$	turn-off delay time				320	ns	
t_f	current fall time				200	ns	
E_{on}	turn-on energy per pulse				0.9	mJ	
E_{off}	turn-off energy per pulse				0.75	mJ	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		60	ns	
t_r	current rise time				35	ns	
$t_{d(off)}$	turn-off delay time				360	ns	
t_f	current fall time				340	ns	
E_{on}	turn-on energy per pulse				1.55	mJ	
E_{off}	turn-off energy per pulse				1.1	mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega; I_C = 20\text{ A}; T_{VJ} = 125^{\circ}\text{C}$			$V_{CEK} \leq V_{CES} - L_S \cdot di/dt$	V	
I_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega; t_p = 10\ \mu\text{s};$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$		40	A	
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.9	K/W	
R_{thCH}	thermal resistance case to heatsink				0.65	K/W	

Output Inverter D1 - D6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$		1200	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$		24	A
I_{F80}			$T_C = 80^{\circ}\text{C}$		16	A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.0 1.6	2.4	V V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -300\text{ A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		1.9	μC
I_{RM}	max. reverse recovery current				12.8	A
t_{rr}	reverse recovery time				335	ns
E_{rec}	reverse recovery energy				0.54	mJ
R_{thJC}	thermal resistance junction to case	(per diode)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.55	K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake T7
Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit	
V_{CES}	collector emitter voltage				1200	V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current		$T_C = 25^\circ\text{C}$		17	A	
I_{C80}			$T_C = 80^\circ\text{C}$		12	A	
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		70	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.9 2.3	2.2	V V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.3\text{ A}; V_{GE} = V_{CE}$	$T_{VJ} = 25^\circ\text{C}$	5	5.5	6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.8	0.6 mA mA	
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			150	nA	
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		600		pF	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		54		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 25^\circ\text{C}$	55		ns	
t_r	current rise time			30		ns	
$t_{d(off)}$	turn-off delay time			320		ns	
t_f	current fall time			200		ns	
E_{on}	turn-on energy per pulse			0.9		mJ	
E_{off}	turn-off energy per pulse			0.75		mJ	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega$	$T_{VJ} = 125^\circ\text{C}$	60		ns	
t_r	current rise time			35		ns	
$t_{d(off)}$	turn-off delay time			360		ns	
t_f	current fall time			340		ns	
E_{on}	turn-on energy per pulse			1.55		mJ	
E_{off}	turn-off energy per pulse			1.1		mJ	
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega; I_C = 20\text{ A}; T_{VJ} = 125^\circ\text{C}$		$V_{CEK} \leq V_{CES} - L_S \cdot di/dt$		V	
I_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 100\ \Omega; t_p = 10\ \mu\text{s};$ non-repetitive	$T_{VJ} = 125^\circ\text{C}$	40		A	
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.9	K/W	
R_{thCH}	thermal resistance case to heatsink			0.65		K/W	

Brake Chopper D7
Ratings

Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage				1200	V
I_{F25}	forward current		$T_C = 25^\circ\text{C}$		15	A
I_{F80}			$T_C = 80^\circ\text{C}$		10	A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.5 2.0	3.1	V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		0.2	0.1 mA mA
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = \text{tbd A}/\mu\text{s}$ $I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^\circ\text{C}$	tbd		μC
I_{RM}	max. reverse recovery current			tbd		A
t_{rr}	reverse recovery time			tbd		ns
E_{rec}	reverse recovery energy			tbd		μJ
R_{thJC}	thermal resistance junction to case	(per diode)			2.5	K/W
R_{thCH}	thermal resistance case to heatsink			0.85		K/W

 $T_C = 25^\circ\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D11

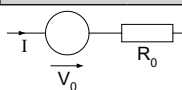
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$		1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^{\circ}\text{C}$		22	A
I_{DAVM}	max. average DC output current	rect.; $d = 1/3$	$T_C = 80^{\circ}\text{C}$		61	A
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		300 tbd	A A
I^2t	I^2t value for fusing	$t = 10\text{ ms}$; sine 50 Hz	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		450 tbd	A^2s A^2s
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$		50	W
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	1.35 1.35	1.6	V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.3	0.01	mA mA
R_{thJC}	thermal resistance junction to case	(per diode)			2.1	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.7		K/W

Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
R_{25}	resistance		$T_C = 25^{\circ}\text{C}$	4.75	5.0	$\text{k}\Omega$
$B_{25/50}$				3375	5.25	K

Module

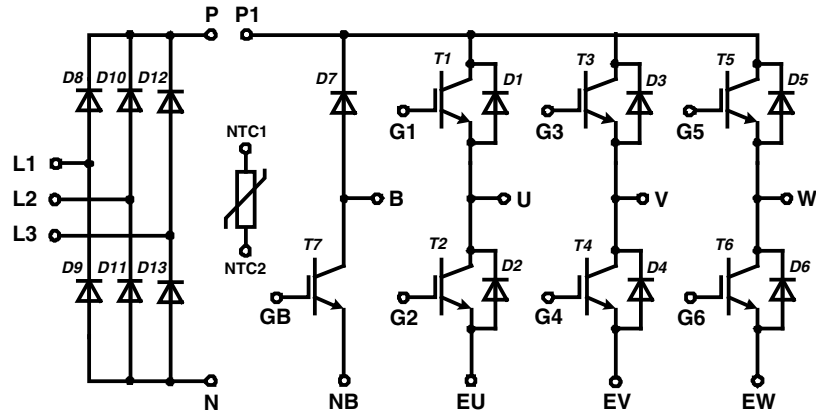
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^{\circ}\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^{\circ}\text{C}$
T_{stg}	storage temperature		-40		125	$^{\circ}\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500	V~
CTI	comparative tracking index				-	
F_C	mounting force		40		80	N
d_S	creep distance on surface		12.7			mm
d_A	strike distance through air		12			mm
Weight				35		g

Equivalent Circuits for Simulation


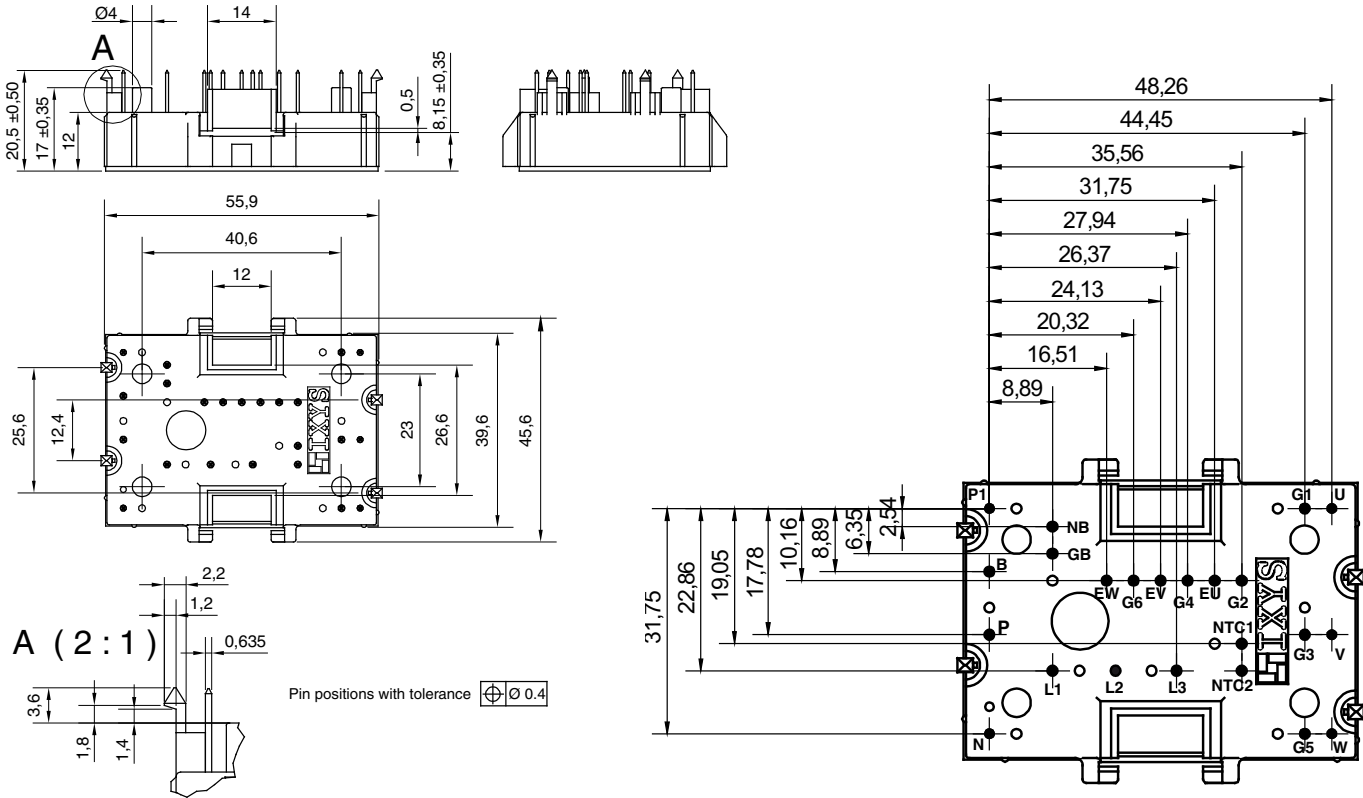
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^{\circ}\text{C}$	0.9		V
R_0				16		$\text{m}\Omega$
V_0	IGBT	T1 - T6	$T_{VJ} = 125^{\circ}\text{C}$	1.0		V
R_0				125		$\text{m}\Omega$
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^{\circ}\text{C}$	1.15		V
R_0				45		$\text{m}\Omega$
V_0	IGBT	T7	$T_{VJ} = 125^{\circ}\text{C}$	1.0		V
R_0				125		$\text{m}\Omega$
V_0	free wheeling diode	D7	$T_{VJ} = 125^{\circ}\text{C}$	1.4		V
R_0				60		$\text{m}\Omega$

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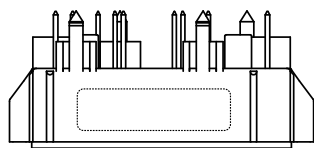
Circuit Diagram



Outline Drawing Dimensions in mm (1 mm = 0.0394")

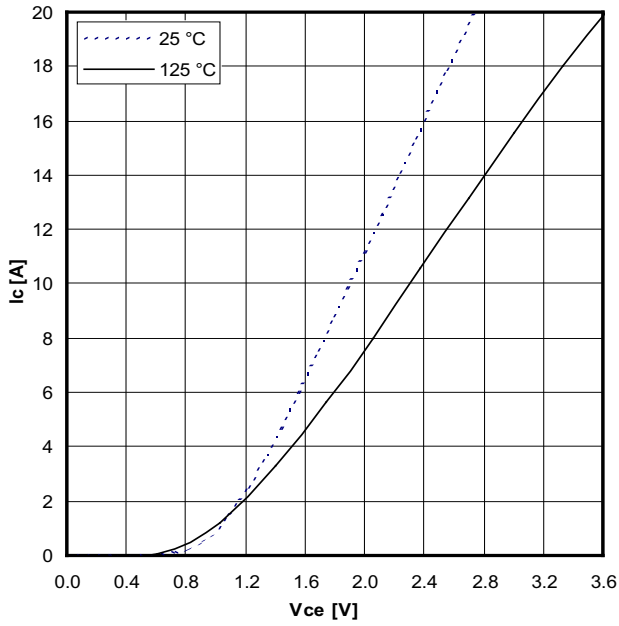


Product Marking

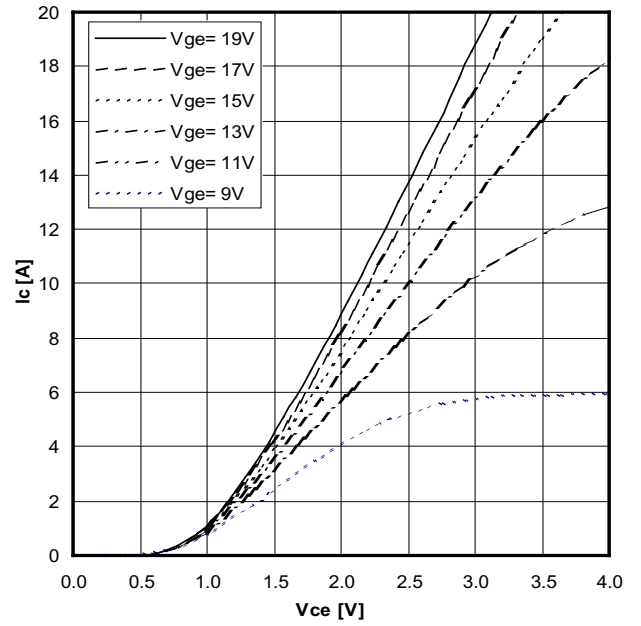


- Part number**
- M = Module
 - I = IGBT
 - T = Trench
 - B = Gen³ / low loss
 - 10 = Current Rating [A]
 - WB = 6-Pack + 3- Rectifier Bridge & Brake Unit
 - 1200 = Reverse Voltage [V]
 - T = NTC
 - MH = MiniPack2

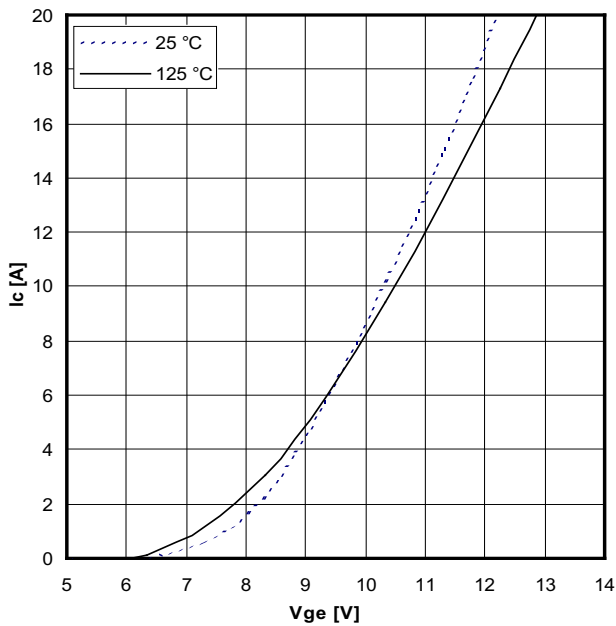
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Standard	MITB 10 WB 1200 TMH	MITB10WB1200TMH	Box	20	502722



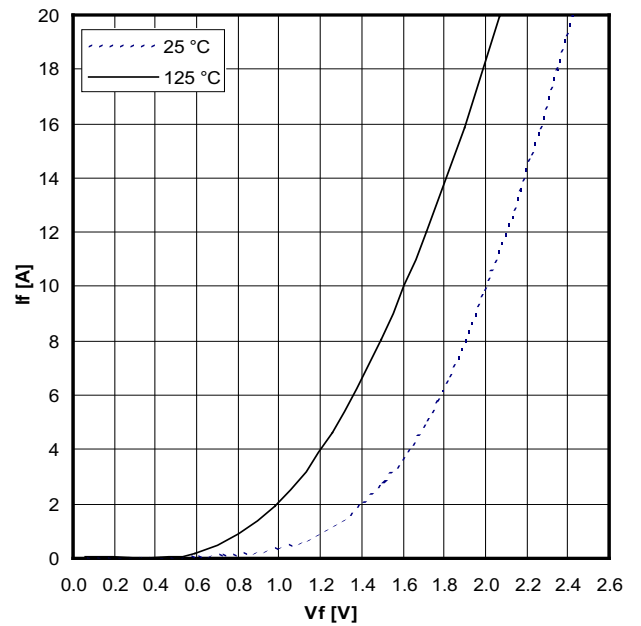
Typical output characteristics, $V_{GE} = 15 V$



Typical output characteristics (125°C)

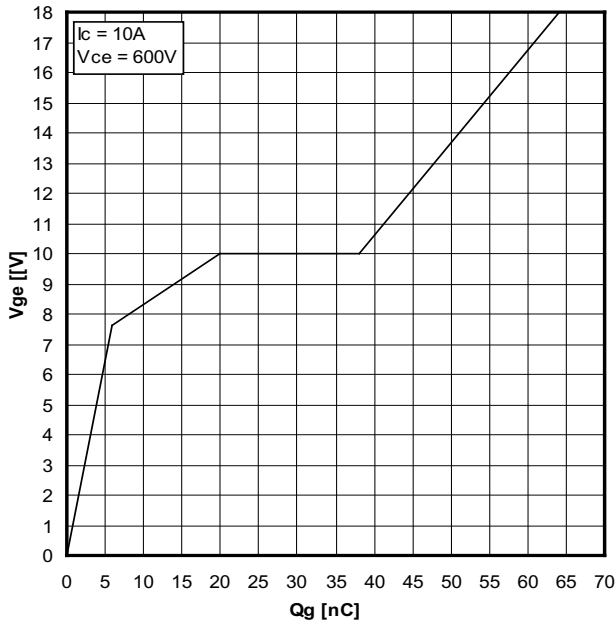


Typical transfer characteristics

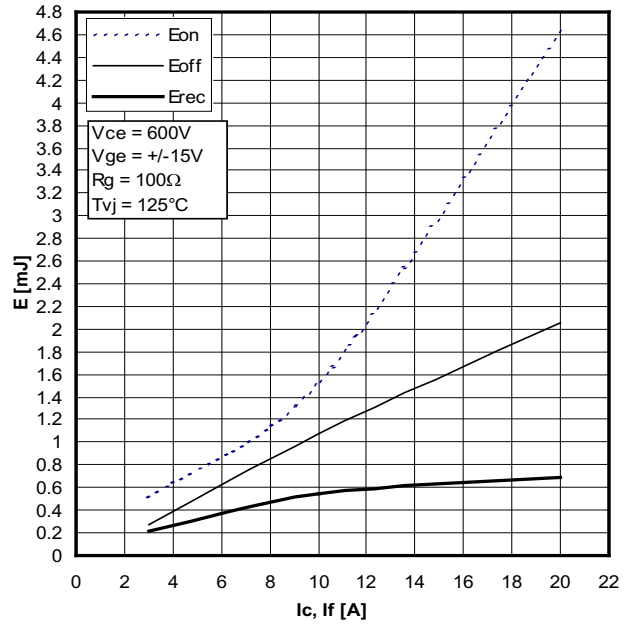


Typical forward characteristics of freewheeling diode

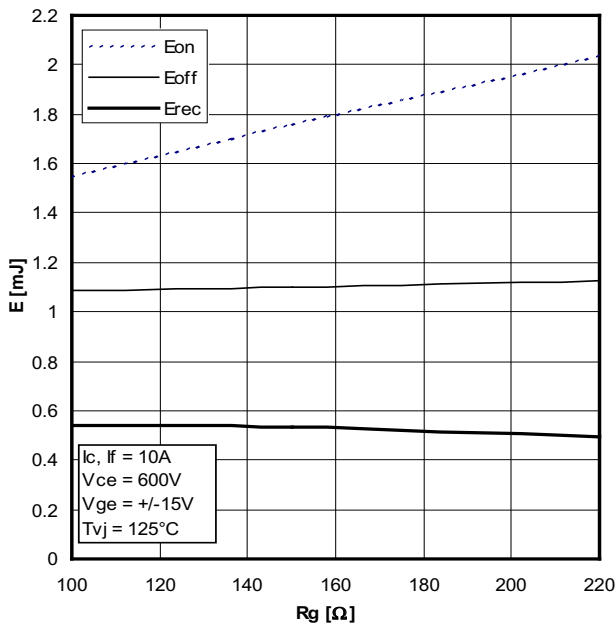
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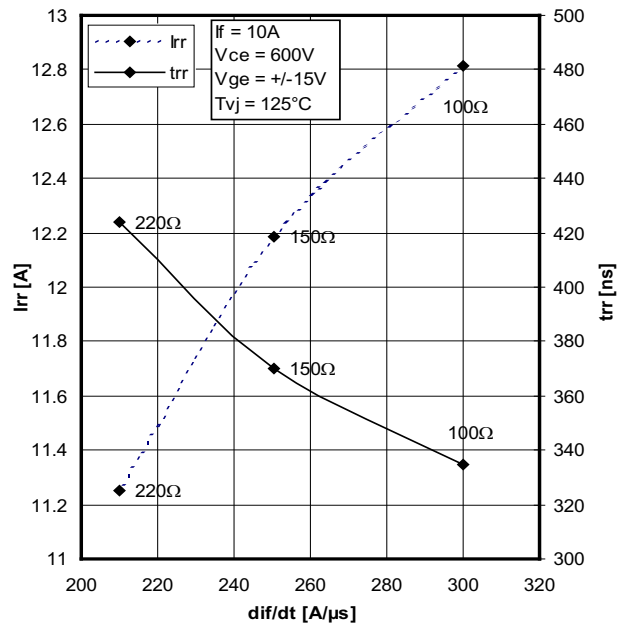
Typical turn on gate charge



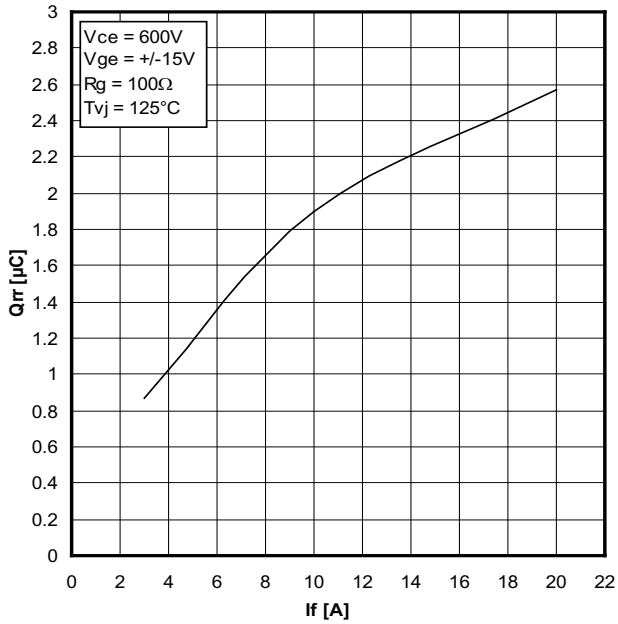
Typical switching energy versus collector current



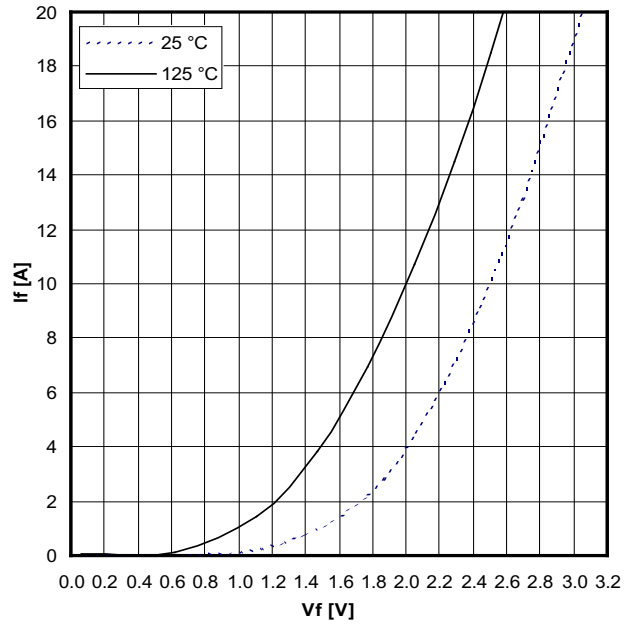
Typical switching energy versus gate resistance



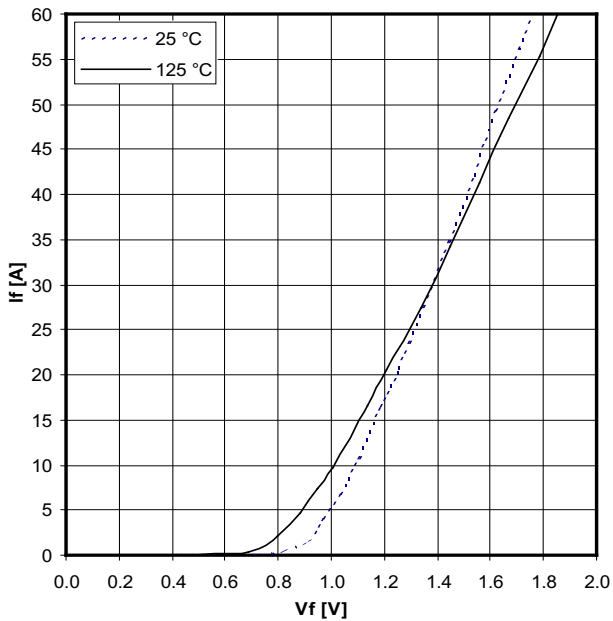
Typical turn-off characteristics of free wheeling diode



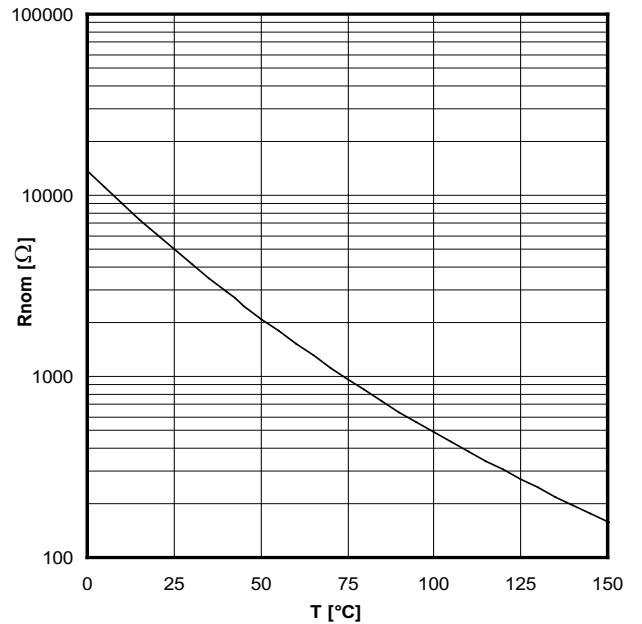
Typical turn-off characteristics of free wheeling diode



Typical forward characteristics of brake diode



Typical forward characteristics per rectifier



Typical thermistor resistance versus temperature